



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

33 A

Features

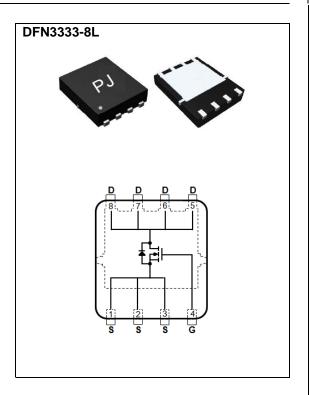
- R_{DS(ON)}, V_{GS}@10V, I_D@15A<21mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@8A<24m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current(Note 4)	Tc=25°C	I _D	33	А	
	T _C =100°C		21		
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	132		
Power Dissipation	T _C =25°C	Po	53	W	
	Tc=100°C		26		
Continuous Drain Current(Note 4)	T _A =25°C	l _D	6		
	T _A =70°C		5	A	
Power Dissipation	T _A =25°C	Po	2.4	10/	
	T _A =70°C		1.6	W	
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	42	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{0JC}	2.8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.73	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A	-	18	21	mΩ
		V _{GS} =4.5V, I _D =8A	-	21	24	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 7)						
Total Gate Charge	Qg	V _{DS} =30V, I _D =15A, V _{GS} =10V ^(Note 1,2)	-	28	-	nC
Gate-Source Charge	Qgs		-	3.5	-	
Gate-Drain Charge	Q_{gd}	VGS=10 V (***********************************	-	6.5	-	
Input Capacitance	Ciss	. \/ 20\/ .\/ 0\/	-	1680	-	pF
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V, f=1MHZ	-	115	-	
Reverse Transfer Capacitance	Crss	I= IIVIIIZ	-	85	-	
Turn-On Delay Time	td _(on)	\/ 20\/ I 4A	-	7.2	-	
Turn-On Rise Time	tr	V _{DD} =30V, I _D =1A,	-	38	-	ns
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=6\Omega$ (Note 1,2)	-	34	-	
Turn-Off Fall Time	t _f	(**************************************	-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I.		-	-	33	А
Diode Forward Current	I _S					
Reverse Recovery Time	V _{SD}	I _S =1A, V _{GS} =0V	-	0.68	1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=29A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

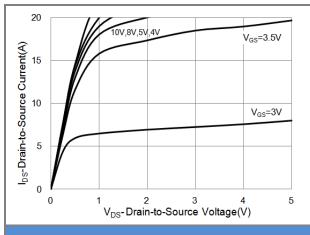


Fig.1 On-Region Characteristics

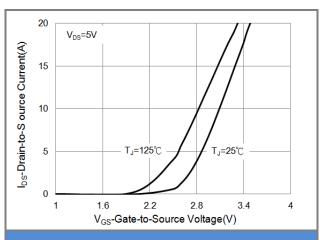


Fig.2 Transfer Characteristics

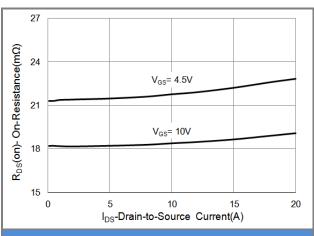


Fig.3 On-Resistance vs. Drain Current

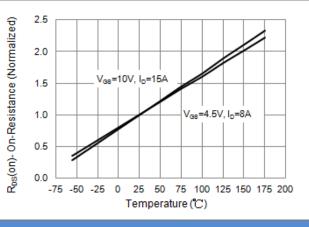


Fig.4 On-Resistance vs. Junction temperature

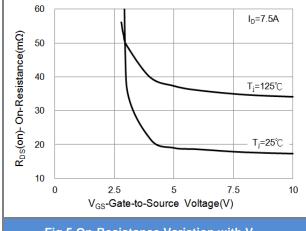


Fig.5 On-Resistance Variation with V_{GS}

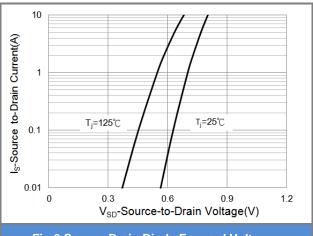


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

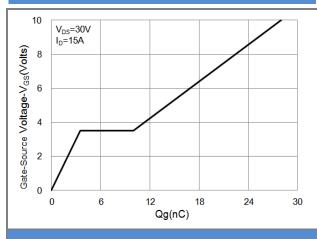


Fig.7 Gate-Charge Characteristics

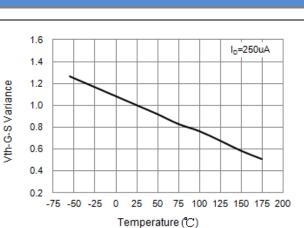
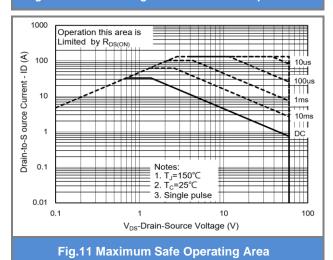


Fig.9 Threshold Voltage Variation with Temperature



1.1 | Indicate | Indic

Fig.8 Breakdown Voltage Variation vs. Temperature

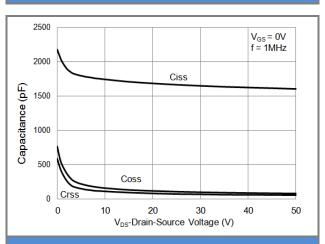


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

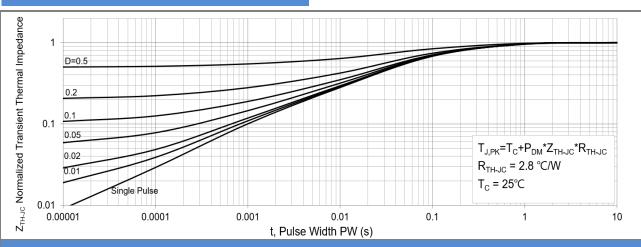


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

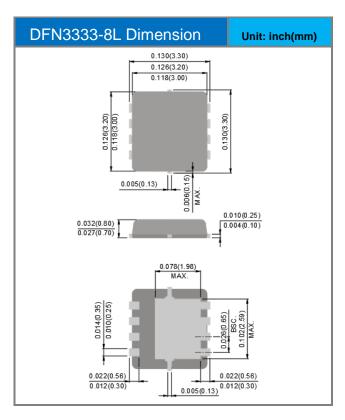


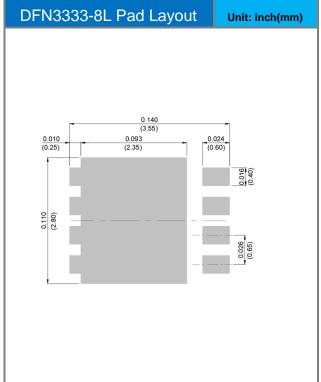


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4466AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4466	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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